



**LIST OF REFERENCES CITED BY APPLICANT**  
(Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION NO.:
4717-12500	10/716,901
APPLICANT:	
Bruce FAURE	
FILING DATE:	GROUP:
November 18, 2003	2812

**U.S. PATENT DOCUMENTS**

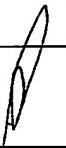
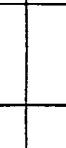
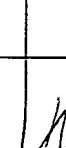
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,374,564	12/1994	Bruel	437	24	
	AB	6,051,849	4/2000	Davis et al.	257	103	
	AC	6,086,673	7/2000	Molnarq	117	102	
	AD	6,113,685	9/2000	Wang et al.	117	3	
	AE	6,146,457	11/2000	Solomon	117	90	
	AF	6,303,405 B1	10/2001	Yoshida et al.	438	46	
	AG	6,440,823 B1	8/2002	Vaudo et al.	438	478	
	AH	6,478,871 B1	11/2002	Shealy et al.	117	84	
	AI	2002/0068201 A1	6/2002	Vaudo et al.	428	704	
	AJ	2002/0011599 A1	1/2002	Motoki et al.	257	76	

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	AK	EP 1 361 298 A1	11/2003	Europe			X
	AL	EP 1 298 234 A2	4/2002	Europe			X
	AM	FR 2 810 159 A1	12/2001	France			X
	AN	FR 2 774 511	8/1999	France			X
	AO	FR 2 681 472	3/1993	France			X
	AP	JP 2002343718 with English Abstract	11/2002	Japan			X
	AQ	WO 02064865 A1 with English Abstract	8/2002	PCT			X
	AR	WO 03/043066 A2	5/2003	PCT			X

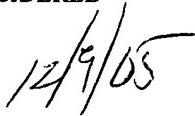
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**OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)**

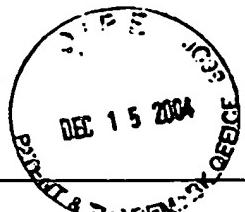
	AS	R. Lantier et al., "Influence of the first preparation steps on the properties of GaN layers grown on 6H-SiC by MBE", , MRS Internet J. Nitride Semicond. Res. 4S1, G3.50 (1999)
	AT	J. Cao et al, "Improved quality GaN by growth on compliant silicon-on-insulator substrates using metalorganic chemical vapor deposition", , Journal of Applied Physics, Vol. 83, No.7, (1998).
	AU	Jyh-Rong Gong et al., "Influence of AlN/GaN strained multi-layers on threading dislocations in GaN films grown by alternate supply of metalorganics and NH <sub>3</sub> ", Materials Science and Engineering B94 pp. 155-1 58 (2002),
	AV	Motoaki Iwaya et al., "Realization of crack-free and high-quality thick Al <sub>x</sub> Ga <sub>1-x</sub> N for UV optoelectronics using low-temperature interlayer", Applied Surface Science Vol.159-160 pp. 405-413 (2000)
	AW	H. Amano et al., "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer", Applied Physics Letters, Vol. 48, No. 5, pp. 353-355 (1986)
	AX	Y. Ujiie et al., "Epitaxial lateral overgrowth of GaAs on a Si substrate", Japanese Journal of Applied-Physics, Vol. 28, No. 3; pp. L337-L339 (1989)
	AY	B. Beaumont, Ph. et al., "Epitaxial lateral overgrowth of GaN", phys. stat. sol. (b) 227, No. 1, 1-43 (2001)
	AZ	

EXAMINER

DATE CONSIDERED

12/9/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	AA	5,714,395	2/1998	Bruel	437	24		
	AB							
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES      NO	
	AC	EP 0 382 341	8/1990	Europe			X	
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	AE							
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